

HEXFET® Power MOSFET, 180 A


SOT-227
FEATURES

- Fully isolated package
- Easy to use and parallel
- Very low on-resistance
- Dynamic dV/dt rating
- Fully avalanche rated
- Simple drive requirements
- Low drain to case capacitance
- Low internal inductance
- UL pending
- Totally lead (Pb)-free


**RoHS
COMPLIANT**
PRODUCT SUMMARY

V_{DSS}	100 V
I_D DC	180 A
$R_{DS(on)}$	0.0065 Ω

DESCRIPTION

5th Generation, high current density HEXFETs® are paralleled into a compact, high power module providing the best combination of switching, ruggedized design, very low on resistance and cost effectiveness.

The isolated SOT-227 package is preferred for all commercial-industrial applications at power dissipation levels to approximately 500 W. The low thermal resistance and easy connection to the SOT-227 package contribute to its universal acceptance throughout the industry.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Continuous drain current at V_{GS} 10 V	I_D	$T_C = 25\text{ }^\circ\text{C}$	180	A
		$T_C = 100\text{ }^\circ\text{C}$	120	
Pulsed drain current	$I_{DM}^{(1)}$		720	
Power dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	480	W
Linear derating factor			2.7	W/°C
Gate to source voltage	V_{GS}		± 20	V
Single pulse avalanche energy	$E_{AS}^{(2)}$		700	mJ
Avalanche current	$I_{AR}^{(1)}$		180	A
Repetitive avalanche energy	$E_{AR}^{(1)}$		48	mJ
Peak diode recovery dV/dt	dV/dt ⁽³⁾		5.7	V/ns
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C
Insulation withstand voltage (AC-RMS)	V_{ISO}		2.5	kV
Mounting torque		M4 screw	1.3	Nm

Notes

(1) Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

(2) Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 43\text{ }\mu\text{H}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 180\text{ A}$ (see fig. 12)

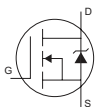
(3) $I_{SD} \leq 180\text{ A}$, $di/dt \leq 83\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150\text{ }^\circ\text{C}$

THERMAL RESISTANCE				
PARAMETER	SYMBOL	TYP.	MAX.	UNITS
Junction to case	$R_{\theta JC}$	-	0.26	°C/W
Case to sink, flat, greased surface	$R_{\theta CS}$	0.05	-	

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ °C}$ unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain to source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	100	-	-	V
Breakdown voltage temperature coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to 25 °C , $I_D = 1\text{ mA}$	-	0.093	-	V/°C
Static drain to source on-resistance	$R_{DS(on)}^{(1)}$	$V_{GS} = 10\text{ V}$, $I_D = 180\text{ A}$	-	0.0065	-	Ω
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Forward transconductance	g_{fs}	$V_{DS} = 25\text{ V}$, $I_D = 180\text{ A}$	93	-	-	S
Drain to source leakage current	I_{DSS}	$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	50	μA
		$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ °C}$	-	-	500	
Gate to source forward leakage	I_{GSS}	$V_{GS} = 20\text{ V}$	-	-	200	nA
		$V_{GS} = -20\text{ V}$	-	-	-200	
Total gate charge	Q_g	$I_D = 180\text{ A}$ $V_{DS} = 80\text{ V}$ $V_{GS} = 10.0\text{ V}$; see fig. 6 and 13 ⁽¹⁾	-	250	380	nC
Gate to source charge	Q_{gs}		-	40	60	
Gate to drain ("Miller") charge	Q_{gd}		-	110	165	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{ V}$ $I_D = 180\text{ A}$ $R_G = 2.0\text{ }\Omega$ (internal) $R_D = 0.27\text{ }\Omega$, see fig. 10 ⁽¹⁾	-	45	-	ns
Rise time	t_r		-	351	-	
Turn-off delay time	$t_{d(off)}$		-	181	-	
Fall time	t_f		-	335	-	
Internal source inductance	L_S	Between lead, and center of die contact	-	5.0	-	nH
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1.0\text{ MHz}$, see fig. 5	-	10 700	-	pF
Output capacitance	C_{oss}		-	2800	-	
Reverse transfer capacitance	C_{rss}		-	1300	-	

Note

⁽¹⁾ Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

SOURCE-DRAIN RATINGS AND CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous source current (body diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 	-	-	180	A
Pulsed source current (body diode)	$I_{SM}^{(1)}$		-	-	720	
Diode forward voltage	$V_{SD}^{(2)}$	$T_J = 25\text{ °C}$, $I_S = 180\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.3	V
Reverse recovery time	$t_{rr}^{(2)}$	$T_J = 25\text{ °C}$, $I_F = 180\text{ A}$; $di/dt = 100\text{ A}/\mu\text{s}$	-	300	450	ns
Reverse recovery charge	Q_{rr}		-	2.6	3.9	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes

⁽¹⁾ Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

⁽²⁾ Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

ORDERING INFORMATION TABLE

Device code	F	B	180	S	A	10	P
	①	②	③	④	⑤	⑥	⑦

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|---|---|---|
| 1 | - | HEXFET® Power MOSFET |
| 2 | - | Generation 5 HEXFET MOSFET silicon DBC construction |
| 3 | - | Current rating (180 = 180 A) |
| 4 | - | Single switch |
| 5 | - | SOT-227 |
| 6 | - | Voltage rating (10 = 100 V) |
| 7 | - | P = Lead (Pb)-free |

CIRCUIT CONFIGURATION
